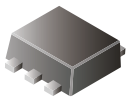
CDSH6-16-G

RoHS Device



Features

-Fast Switching Speed

-For general purpose switching applications.

-High conductance.

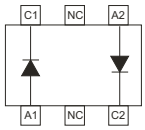
Mechanical data

-Case: SOT-563, Molded Plastic

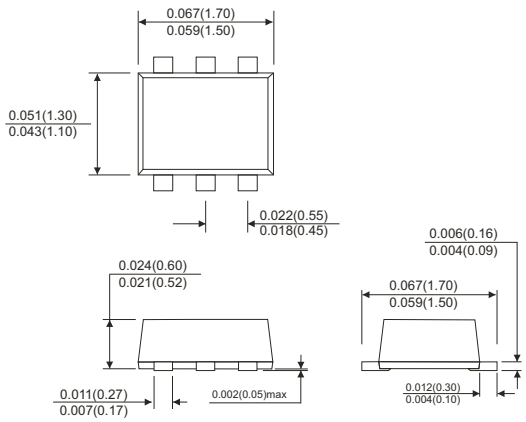
-Terminals: Solderable per MIL-STD-202, Method 208

Marking: KAM

Circuit diagram



SOT-563



Dimensions in inches and (millimeters)

Maximum Ratings (at TA=25°C unless otherwise noted)

Parameter	Symbol	Max	Unit
Non-repetitive peak reverse voltage	V_{RM}	100	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V_{RRM} V_{RWM} V_R	75	V
RMS reverse voltage	$V_{R(RMS)}$	53	V
Forward continuous current	I_{FM}	300	mA
Averaged rectified output current	I_O	200	mA
Peak forward surge current @t=1.0μs @T=1.0s	I_{FSM}	2 1	A
Power dissipation	P_D	150	mW
Thermal resistance, junction to air	$R_{\theta JA}$	833	°C/W
Junction temperature	T_J	150	°C
Storage temperature	T_{STG}	-65 to +150	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Reverse breakdown voltage	I_R=100μA	V_{BR}	75		V
Reverse voltage leakage current	V_R=75V V_R=20V	I_R		1 25	μA nA
Forward voltage	I_F=1mA I_F=10mA I_F=50mA I_F=150mA	V_F		0.715 0.855 1 1.25	V
Diode capacitance	V_R=0V, f=1MHz	C_T		2	pF
Reverse recovery time	I_F=I_R=10mA, I_{rr}=0.1xI_R, R_L=100Ω	t_{rr}		4	nS

Typical Characteristics (CDSH6-16-G)

Fig.1 - Forward Power Derating Curve

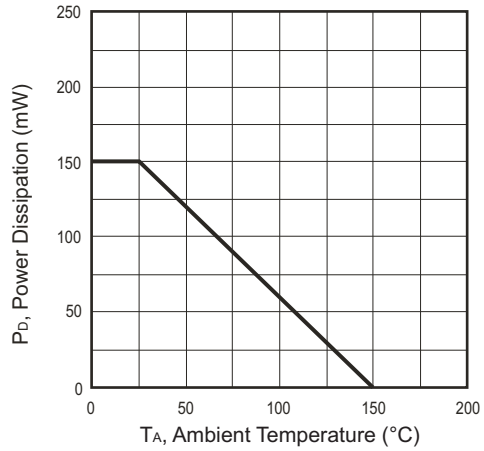


Fig.2 - Typical Forward Characteristics

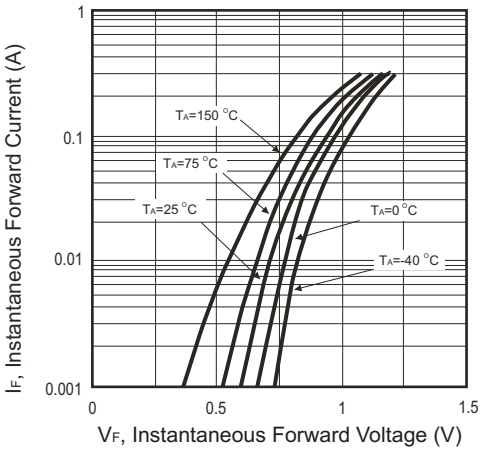


Fig.3 - Typical Diode Capacitance Characteristics

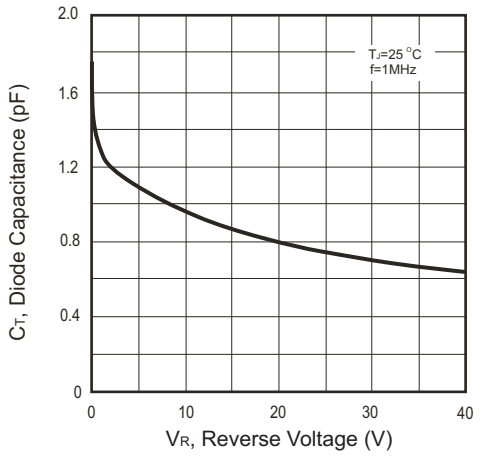


Fig.4 - Typical Reverse Current Characteristics